



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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SOT89 NPN SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

FCX658A

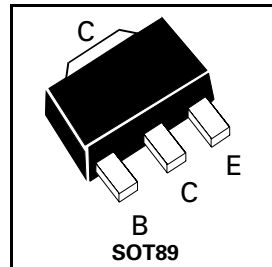
ISSUE 1 – NOVEMBER 2000

FEATURES

- * 400 Volt V_{CE0}
- * 0.5 Amp continuous current
- * $P_{tot}=1$ Watt
- * Optimised h_{fe} characterised upto 200mA

APPLICATIONS

- * Telephone dialler circuits
- * Hook switches for modems
- * Predrivers within HID lamp ballasts
- * (SLIC) Subscriber Line Interface Cards



Partmarking Detail - 65A

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	1	A
Continuous Collector Current	I_C	500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$ derate above $25^{\circ}C$	P_{tot}	1 5.7	W mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

FCX658A

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	400	480		V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	400	465		V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	7.8		V	$I_E = 100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			100	nA	$V_{CB} = 320\text{V}$
Collector Cut-Off Current	I_{CES}			100	nA	$V_{CE} = 320\text{V}$
Emitter Cut-Off Current	I_{EBO}			100	nA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.165 0.125 0.2	V V V	$I_C = 20\text{mA}, I_B = 1\text{mA}$ $I_C = 50\text{mA}, I_B = 5\text{mA}^*$ $I_C = 100\text{mA}, I_B = 10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.75	0.85	V	$I_C = 100\text{mA}, I_B = 10\text{mA}^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		0.70	0.85	V	$I_C = 100\text{mA}, V_{CE} = 5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	85 100 55 35	150 170 130 90			$I_C = 1\text{mA}, V_{CE} = 5\text{V}^*$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}^*$ $I_C = 100\text{mA}, V_{CE} = 5\text{V}^*$ $I_C = 200\text{mA}, V_{CE} = 10\text{V}^*$
Transition Frequency	f_T	50			MHz	$I_C = 20\text{mA}, V_{CE} = 20\text{V}$ $f = 20\text{MHz}$
Output Capacitance	C_{obo}			10	pF	$V_{CB} = 20\text{V}, f = 1\text{MHz}$
Switching times	t_{on} t_{off}		130 3300		ns ns	$I_C = 100\text{mA}, V_{CE} = 100\text{V}$ $I_{B1} = 10\text{mA}, I_{B2} = -20\text{mA}$

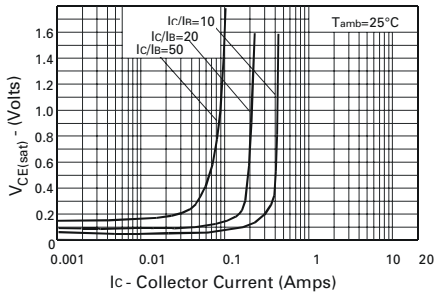
* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

NB

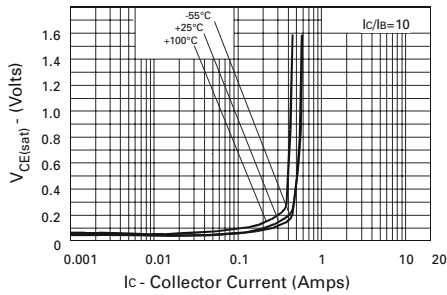
For high voltage applications the appropriate industry sector PCB guidelines should be considered with regard to voltage spacing between conductors.

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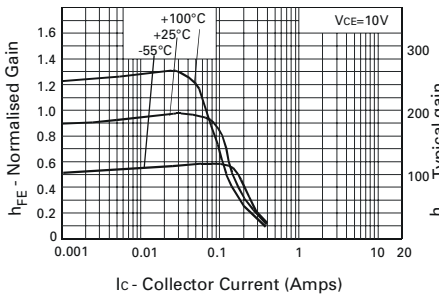
TYPICAL CHARACTERISTICS



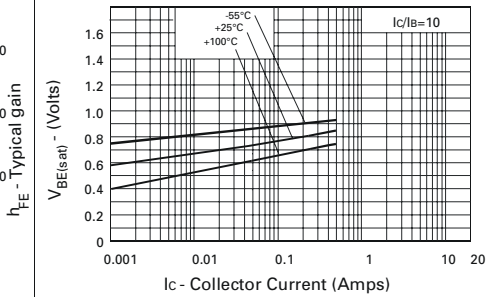
$V_{CE(sat)}$ v I_C



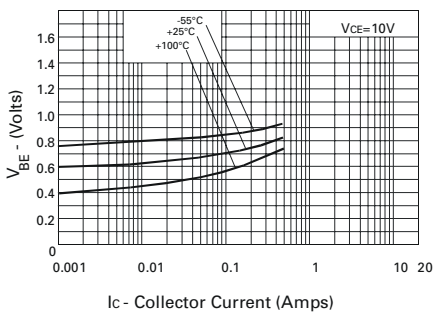
$V_{CE(sat)}$ v I_C



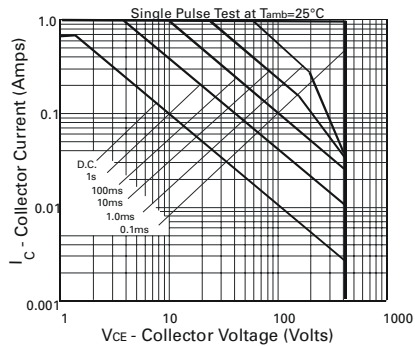
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C

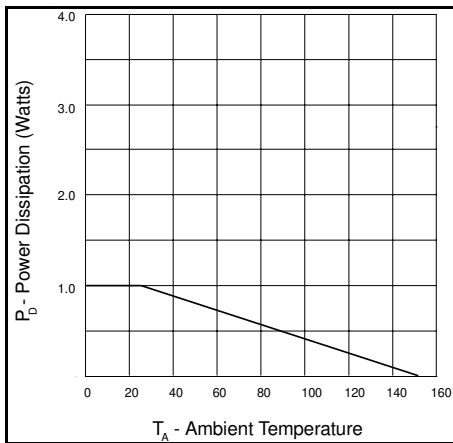


Safe Operating Area

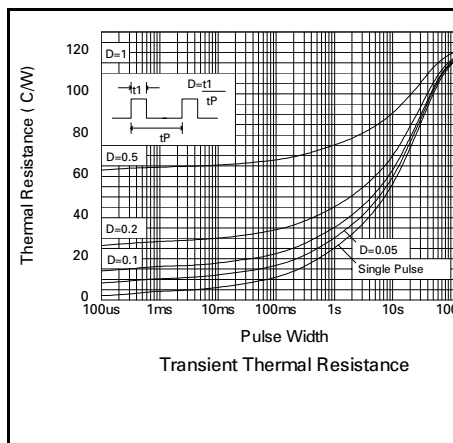
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THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient ₁ Junction to Case	$R_{th(j-amb)1}$ $R_{th(j-case)}$	125 10	°C/W °C/W



SOT89 (1W) Derating



Transient thermal resistance for a Zetex 1W SOT89 device mounted on a 15 mm x 15 mm ceramic substrate



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